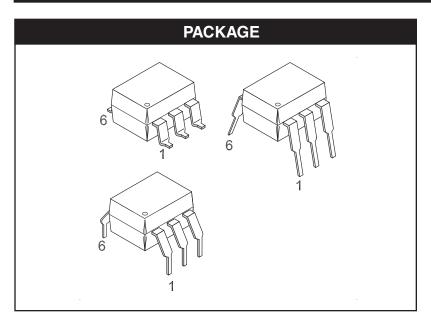
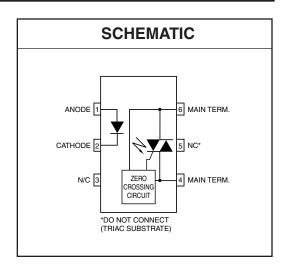


MOC3081M MOC3082M MOC3083M





#### **DESCRIPTION**

The MOC3081M, MOC3082M and MOC3083M devices consist of a GaAs infrared emitting diode optically coupled to a monolithic silicon detector performing the function of a zero voltage crossing bilateral triac driver.

They are designed for use with a discrete power triac in the interface of logic systems to equipment powered from 240 VAC lines, such as solid-state relays, industrial controls, motors, solenoids and consumer appliances, etc.

#### **FEATURES**

- Underwriters Laboratories (UL) recognized file #E90700, Volume 2
- VDE recognized file #102497 add option V (e.g., MOC3083VM)
- Simplifies logic control of 240 VAC power
- Zero voltage crossing
- dv/dt of 1500 V/µs typical, 600 V/µs guaranteed
- Compatible with Fairchild's FKPF12N80 discrete power triac

#### **APPLICATIONS**

- Solenoid/valve controls
- Lighting controls
- Static power switches
- AC motor drives
- · Temperature controls
- E.M. contactors
- AC motor starters
- Solid state relays

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Parameters	Symbol	Value	Units	
TOTAL DEVICE				
Storage Temperature	T <sub>STG</sub>	-40 to +150	°C	
Operating Temperature	T <sub>OPR</sub>	-40 to +85	°C	
Lead Solder Temperature	T <sub>SOL</sub>	260 for 10 sec	°C	
Junction Temperature Range	T <sub>J</sub>	-40 to +100	°C	
Isolation Surge Voltage <sup>(4)</sup> (peak AC voltage, 60Hz, 1 sec duration)	V <sub>ISO</sub>	7500	Vac(pk)	
Total Device Power Dissipation @ 25°C	ь	250	mW	
Derate above 25°C	P <sub>D</sub>	2.94	mW/°C	
EMITTER				
Continuous Forward Current	I <sub>F</sub>	60	mA	
Reverse Voltage	V <sub>R</sub>	6	V	
Total Power Dissipation 25°C Ambient	В	120	mW	
Derate above 25°C	P <sub>D</sub>	1.41	mW/°C	
DETECTOR				
Off-State Output Terminal Voltage	V <sub>DRM</sub>	800	V	
Peak Repetitive Surge Current (PW = 100 μs, 120 pps)	I <sub>TSM</sub>	1	Α	
Total Power Dissipation @ 25°C Ambient	Ь	150	mW	
Derate above 25°C	P <sub>D</sub>	1.76	mW/°C	

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### **ELECTRICAL CHARACTERISTICS** ( $T_A = 25$ °C Unless otherwise specified)

INDIVIDUAL COMPONENT CHARACTERISTICS								
Parameters	Test Conditions	Symbol	Min	Тур*	Max	Units		
EMITTER								
Input Forward Voltage	$I_F = 30 \text{ mA}$	V <sub>F</sub>		1.3	1.5	V		
Reverse Leakage Current	V <sub>R</sub> = 6 V	I <sub>R</sub>		0.005	100	μΑ		
DETECTOR								
Peak Blocking Current, Either Direction	$V_{DRM} = 800V, I_F = 0 \text{ (note 1)}$	I <sub>DRM1</sub>		10	500	nA		
Critical Rate of Rise of Off-State Voltage	I <sub>F</sub> = 0 (figure 9, note 3)	dv/dt	600	1500		V/µs		

<b>TRANSFER CHARACTERISTICS</b> (T <sub>A</sub> = 25°C Unless otherwise specified.)								
DC Characteristics	Test Conditions	Symbol	Device	Device Min		Max	Units	
LED Trigger Current	Main Terminal Voltage = 3V (note 2)	I <sub>FT</sub>	MOC3081M			15		
			MOC3082M			10	mA	
			MOC3083M			5		
Peak On-State Voltage, Either Direction	$I_{TM} = 100 \text{ mA peak},$ $I_F = \text{rated } I_{FT}$	V <sub>TM</sub>	All		1.8	3	V	
Holding Current, Either Direction		I <sub>H</sub>	All		500		μΑ	

<b>ZERO CROSSING CHARACTERISTICS</b> (T <sub>A</sub> = 25°C Unless otherwise specified.)								
DC Characteristics	Test Conditions	Symbol	Device	Min	Тур*	Max	Units	
Inhibit Voltage (MT1-MT2 voltage above which device will not trigger)	I <sub>F</sub> = Rated I <sub>FT</sub>	V <sub>INH</sub>	All		12	20	V	
Leakage in Inhibited State	$I_F$ = Rated $I_{FT}$ , $V_{DRM}$ = 800V, off state	I <sub>DRM2</sub>	All		200	500	μА	

ISOLATION CHARACTERISTICS								
Characteristics	Test Conditions	Symbol	Min	Тур*	Max	Units		
Input-Output Isolation Voltage	f = 60 Hz, t = 1 sec (note 4)	V <sub>ISO</sub>	7500			Vac(pk)		

<sup>\*</sup>Typical values at  $T_A = 25$ °C

#### Note

- 1. Test voltage must be applied within dv/dt rating.
- 2. All devices are guaranteed to trigger at an  $I_F$  value less than or equal to max  $I_{FT}$ . Therefore, recommended operating  $I_F$  lies between max  $I_{FT}$  (15 mA for MOC3081M, 10 mA for MOC3082M, 5 mA for MOC3083M) and absolute max  $I_F$  (60 mA).
- 3. This is static dv/dt. See Figure 9 for test circuit. Commutating dv/dt is a function of the load-driving thyristor(s) only.
- 4. Isolation surge voltage, V<sub>ISO</sub>, is an internal device dielectric breakdown rating. For this test, Pins 1 and 2 are common, and Pins 4, 5 and 6 are common.

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Figure 1. LED Forward Voltage vs. Forward Current

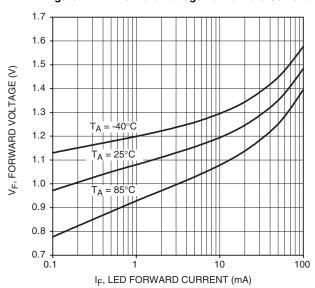


Figure 2. Trigger Current Vs. Temperature

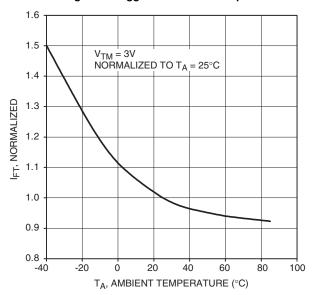


Figure 3. LED Current Required to Trigger vs. LED Pulse Width

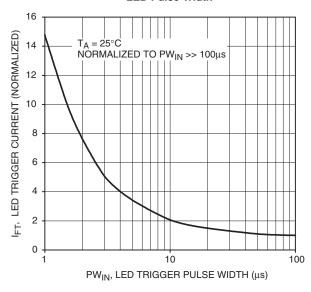


Figure 4. Leakage Current, IDRM vs. Temperature

